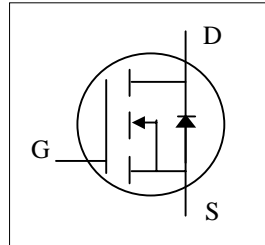
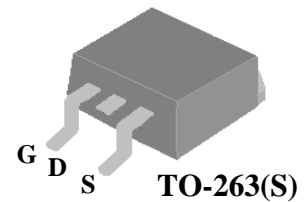




- ▼ 100% R<sub>g</sub> & UIS Test
- ▼ Low t<sub>rr</sub> / Q<sub>rr</sub>
- ▼ Simple Drive Requirement
- ▼ RoHS Compliant & Halogen-Free



BV <sub>DSS</sub>	600V
R <sub>DS(ON)</sub>	115mΩ
I <sub>D</sub> <sup>3</sup>	28A



### Description

AP60SL115D series are from Advanced Power innovated design and silicon process technology to achieve the lowest possible on-resistance and fast switching performance. It provides the designer with an extreme efficient device for use in a wide range of power applications.

The TO-263 package is widely preferred for all commercial-industrial surface mount applications using infrared reflow technique and suited for high current application due to the low connection resistance.

### Absolute Maximum Ratings @T<sub>j</sub>=25°C (unless otherwise specified)

Symbol	Parameter	Rating	Units
V <sub>DS</sub>	Drain-Source Voltage	600	V
V <sub>GS</sub>	Gate-Source Voltage	+20	V
V <sub>GS</sub>	Gate-Source Voltage, AC (f > 1Hz)	+30	V
I <sub>D</sub> @T <sub>C</sub> =25°C	Drain Current, V <sub>GS</sub> @ 10V <sup>3</sup>	28	A
I <sub>D</sub> @T <sub>C</sub> =100°C	Drain Current, V <sub>GS</sub> @ 10V <sup>3</sup>	17.7	A
I <sub>DM</sub>	Pulsed Drain Current <sup>1</sup>	84	A
dv/dt	MOSFET dv/dt Ruggedness (V <sub>DS</sub> = 0 ... 480V )	20	V/ns
P <sub>D</sub> @T <sub>C</sub> =25°C	Total Power Dissipation	178	W
P <sub>D</sub> @T <sub>A</sub> =25°C	Total Power Dissipation <sup>6</sup>	3.12	W
E <sub>AS</sub>	Single Pulse Avalanche Energy <sup>4</sup>	300	mJ
dv/dt	Peak Diode Recovery dv/dt <sup>5</sup>	15	V/ns
T <sub>STG</sub>	Storage Temperature Range	-55 to 150	°C
T <sub>J</sub>	Operating Junction Temperature Range	-55 to 150	°C

### Thermal Data

Symbol	Parameter	Value	Units
R <sub>thj-c</sub>	Maximum Thermal Resistance, Junction-case	0.7	°C/W
R <sub>thj-a</sub>	Maximum Thermal Resistance, Junction-ambient (PCB mount) <sup>6</sup>	40	°C/W



# AP60SL115DS

## Electrical Characteristics @ $T_j=25^{\circ}\text{C}$ (unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
$BV_{DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	600	-	-	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance <sup>2</sup>	$V_{GS}=10V, I_D=9.6A$	-	-	115	m $\Omega$
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu A$	2	-	5	V
$g_{fs}$	Forward Transconductance	$V_{DS}=10V, I_D=14A$	-	21	-	S
$I_{DSS}$	Drain-Source Leakage Current	$V_{DS}=480V, V_{GS}=0V$	-	-	100	$\mu A$
$I_{GSS}$	Gate-Source Leakage	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	$\pm 1$	$\mu A$
$Q_g$	Total Gate Charge	$I_D=14A$	-	91	145	nC
$Q_{gs}$	Gate-Source Charge	$V_{DS}=480V$	-	20	-	nC
$Q_{gd}$	Gate-Drain ("Miller") Charge	$V_{GS}=10V$	-	42	-	nC
$t_{d(on)}$	Turn-on Delay Time	$V_{DD}=300V$	-	22	-	ns
$t_r$	Rise Time	$I_D=14A$	-	34	-	ns
$t_{d(off)}$	Turn-off Delay Time	$R_G=3.3\Omega$	-	89	-	ns
$t_f$	Fall Time	$V_{GS}=10V$	-	31	-	ns
$C_{iss}$	Input Capacitance	$V_{GS}=0V$	-	3200	5120	pF
$C_{oss}$	Output Capacitance	$V_{DS}=100V$	-	100	-	pF
$C_{riss}$	Reverse Transfer Capacitance	$f=1.0\text{MHz}$	-	7	-	pF
$R_g$	Gate Resistance	$f=1.0\text{MHz}$	-	4.2	8.4	$\Omega$

## Source-Drain Diode

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
$V_{SD}$	Forward On Voltage <sup>2</sup>	$I_S=9.6A, V_{GS}=0V$	-	0.85	-	V
$t_{rr}$	Reverse Recovery Time	$I_S=14A, V_{GS}=0V$	-	175	-	ns
$Q_{rr}$	Reverse Recovery Charge	$dI/dt=100A/\mu s$	-	1.7	-	$\mu C$

### Notes:

1. Pulse width limited by max. junction temperature.
2. Pulse test
3. Limited by max. junction temperature. Maximum duty cycle  $D=0.75$
4. Starting  $T_j=25^{\circ}\text{C}$ ,  $V_{DD}=90V$ ,  $L=150\text{mH}$ ,  $R_G=25\Omega$ ,  $V_{GS}=10V$
5.  $I_{SD} \leq I_D$ ,  $V_{DD} \leq BV_{DSS}$ , starting  $T_j = 25^{\circ}\text{C}$
6. Surface mounted on 1 in<sup>2</sup> copper pad of FR4 board

THIS PRODUCT IS SENSITIVE TO ELECTROSTATIC DISCHARGE, PLEASE HANDLE WITH CAUTION.

USE OF THIS PRODUCT AS A CRITICAL COMPONENT IN LIFE SUPPORT OR OTHER SIMILAR SYSTEMS IS NOT AUTHORIZED.

APEC DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS.

APEC RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION OR DESIGN.

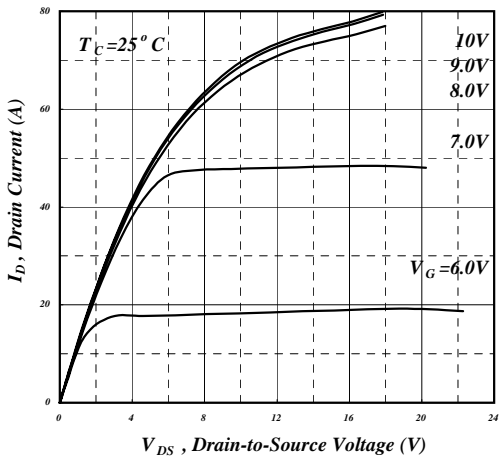


Fig 1. Typical Output Characteristics

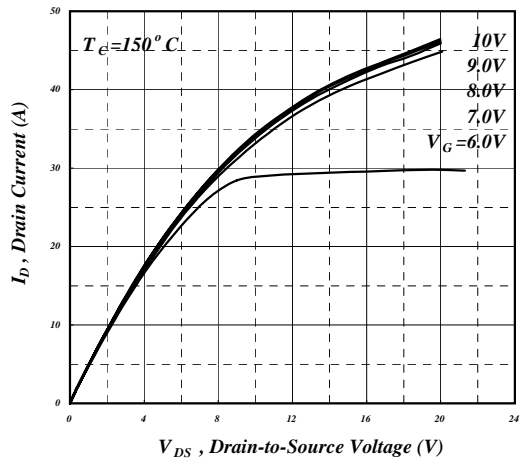


Fig 2. Typical Output Characteristics

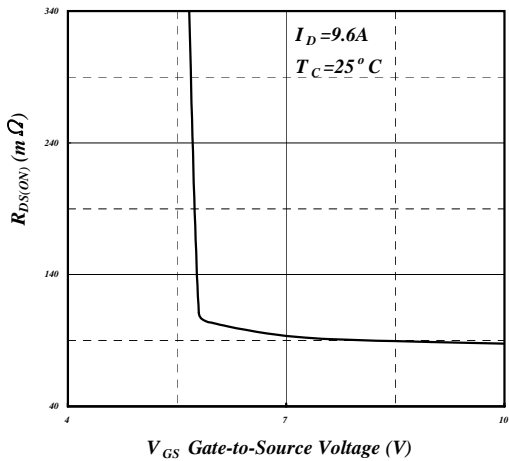


Fig 3. On-Resistance v.s. Gate Voltage

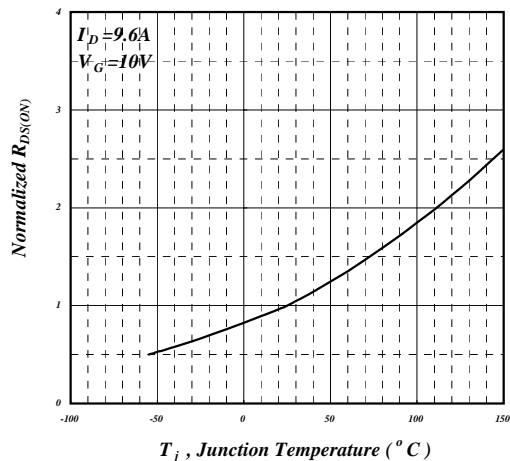


Fig 4. Normalized On-Resistance v.s. Junction Temperature

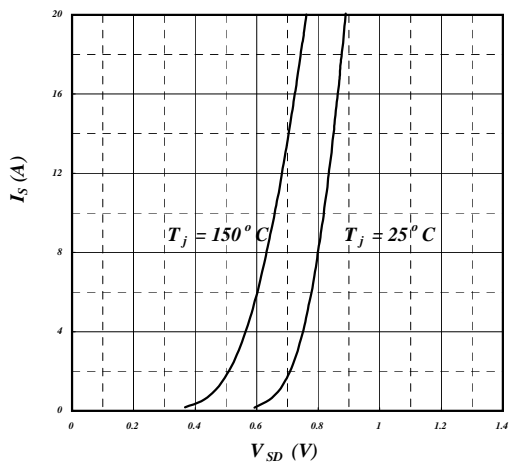


Fig 5. Forward Characteristic of Reverse Diode

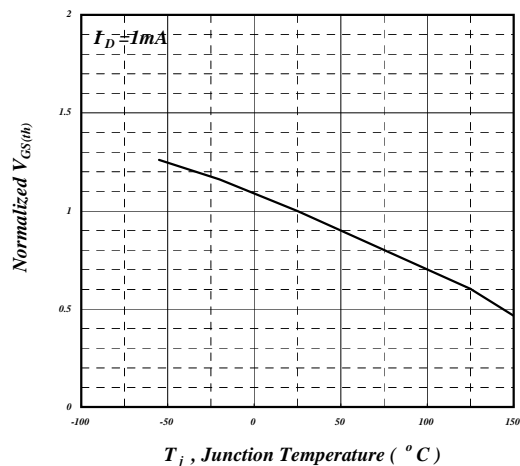


Fig 6. Gate Threshold Voltage v.s. Junction Temperature

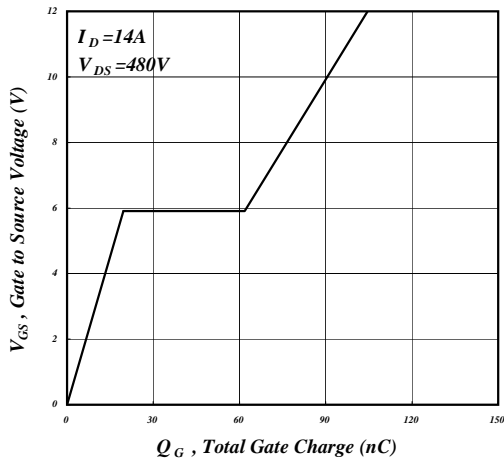


Fig 7. Gate Charge Characteristics

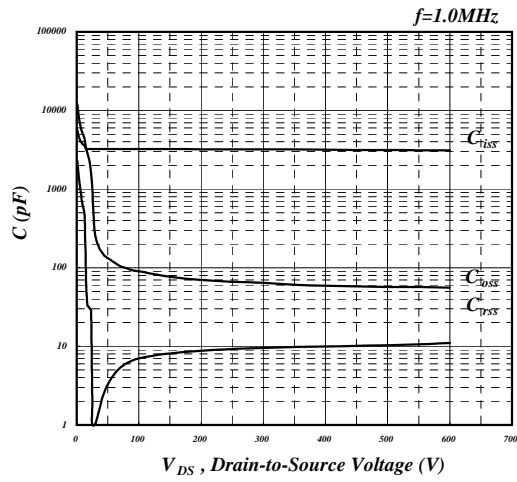


Fig 8. Typical Capacitance Characteristics

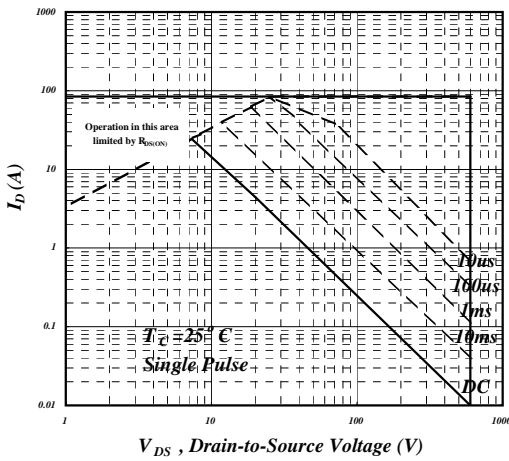


Fig 9. Maximum Safe Operating Area

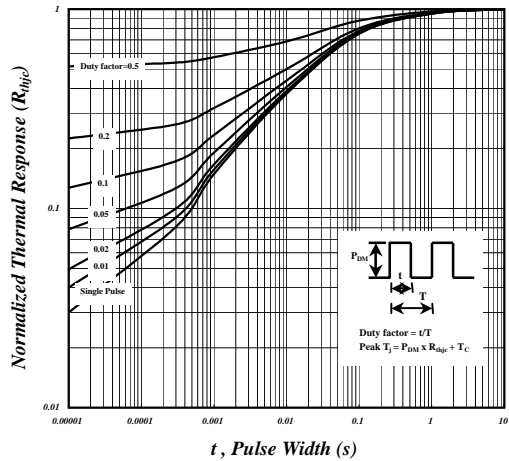


Fig 10. Effective Transient Thermal Impedance

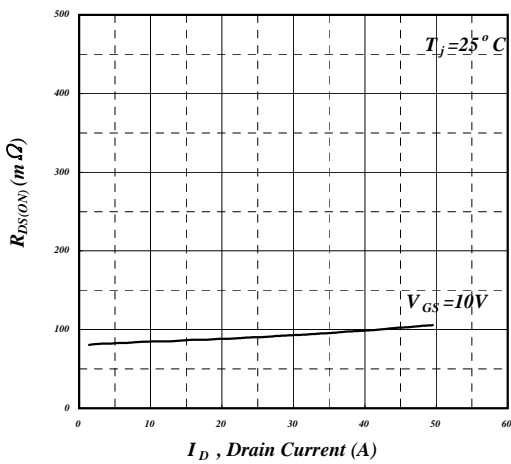


Fig 11. Typ. Drain-Source on State Resistance

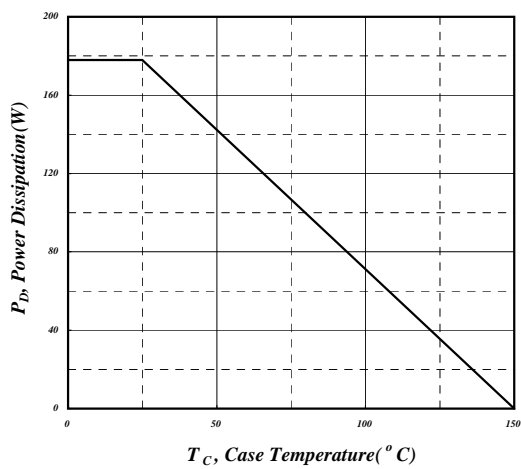
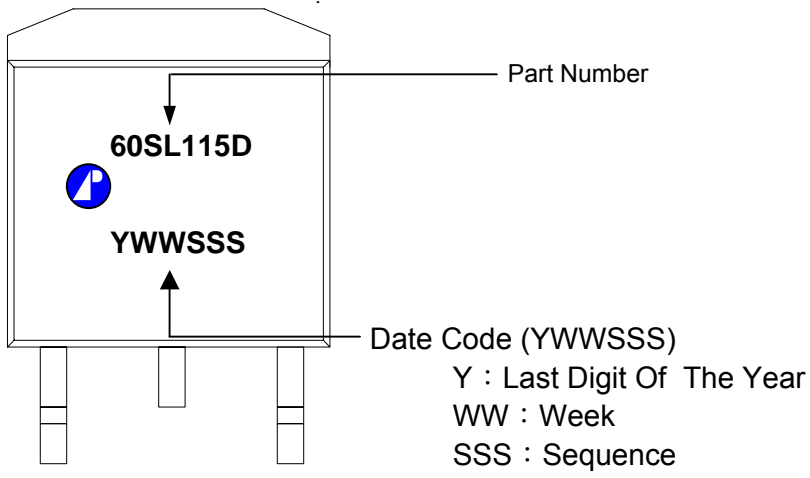


Fig 12. Total Power Dissipation

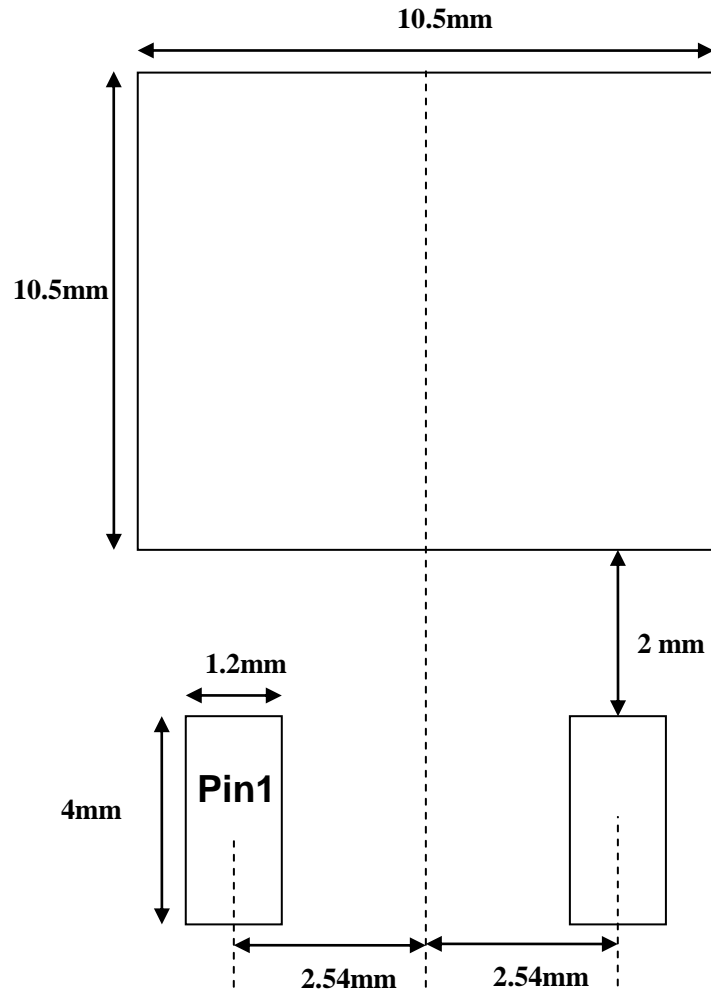


## MARKING INFORMATION



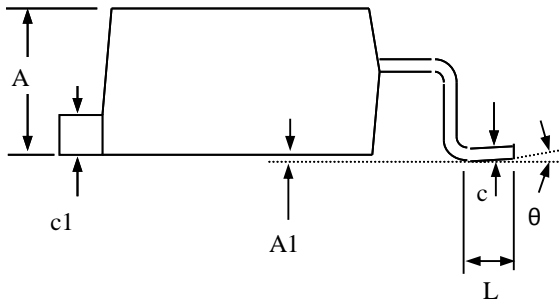
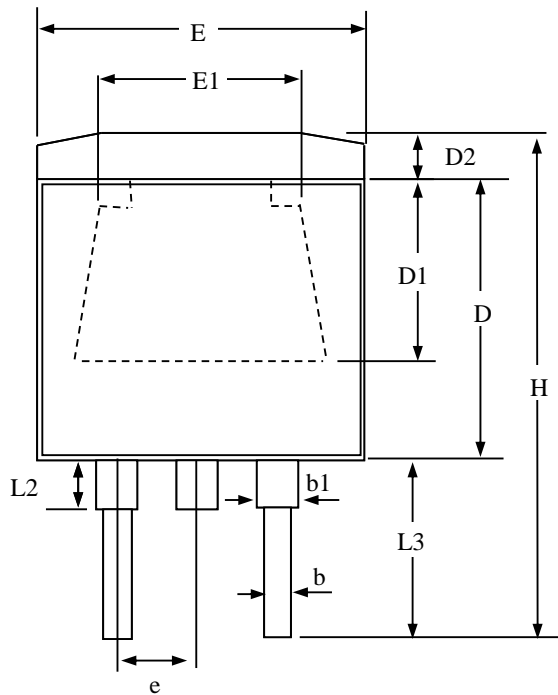


TO-263 FOOTPRINT :





**Package Outline : TO-263**



SYMBOLS	Millimeters		
	MIN	NOM	MAX
A	4.00	4.75	5.20
A1	0.00	0.15	0.30
b	0.50	0.90	1.10
b1	1.07	1.27	1.47
c	0.30	0.55	0.80
c1	1.10	1.40	1.70
D	8.30	9.05	9.80
D1	5.10(ref)		
D2	1.27(ref)		
E	9.50	10.10	10.70
E1	7.00~9.00(ref)		
e	2.04	2.54	3.04
L1	2.54(ref)		
L2	1.5 (ref)		
L3	3.50	4.50	5.50
θ	0°	-----	8°
H	13.07	15.27	16.57

- 1.All Dimensions Are in Millimeters.
- 2.Dimension Does Not Include Mold Protrusions.